

LM124A/LM124QML Low Power Quad Operational Amplifiers

General Description

The LM124/124A consists of four independent, high gain, internally frequency compensated operational amplifiers which were designed specifically to operate from a single power supply over a wide range of voltages. Operation from split power supplies is also possible and the low power supply current drain is independent of the magnitude of the power supply voltage.

Application areas include transducer amplifiers, DC gain blocks and all the conventional op amp circuits which now can be more easily implemented in single power supply systems. For example, the LM124/124A can be directly operated off of the standard +5Vdc power supply voltage which is used in digital systems and will easily provide the required interface electronics without requiring the additional +15Vdc power supplies.

Unique Characteristics

- In the linear mode the input common-mode voltage range includes ground and the output voltage can also swing to ground, even though operated from only a single power supply voltage
- The unity gain cross frequency is temperature compensated
- The input bias current is also temperature compensated

Advantages

- Eliminates need for dual supplies
- Four internally compensated op amps in a single package
- Allows directly sensing near GND and V_{OUT} also goes to GND
- Compatible with all forms of logic
- Power drain suitable for battery operation

Features

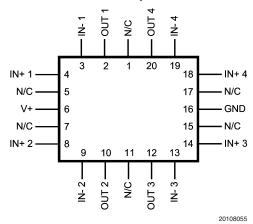
- Internally frequency compensated for unity gain
- Large DC voltage gain 100 dB
- Wide bandwidth (unity gain) 1 MHz (temperature compensated)
- Wide power supply range:
 Single supply 3V to 32V
 or dual supplies ±1.5V to ±16V
- Very low supply current drain (700 µA)—essentially independent of supply voltage
- Low input biasing current 45 nA (temperature compensated)
- Low input offset voltage 2 mV and offset current: 5 nA
- Input common-mode voltage range includes ground
- Differential input voltage range equal to the power supply voltage
- Large output voltage swing 0V to V⁺ 1.5V

Ordering Information

NS PART NUMBER	SMD PART NUMBER	NS PACKAGE NUMBER	PACKAGE DISCRIPTION
LM124J/883	7704301CA	J14A	14LD CERDIP
LM124AE/883	77043022A	E20A	20LD LEADLESS CHIP CARRIER
LM124AJ/883	7704302CA	J14A	14LD CERDIP
LM124AW/883		W14B	14LD CERPACK
LM124AWG/883	7704302XA	WG14A	14LD CERAMIC SOIC
LM124AJLQMLV	5962L9950401VCA,	J14A	14LD CERDIP
	50k rd(Si)		
LM124AJRQMLV	5962R9950401VCA,	J14A	14LD CERDIP
	100k rd(Si)		
LM124AWGLQMLV	5962L9950401VZA,	WG14A	14LD CERAMIC SOIC
	50k rd(Si)		
LM124AWGRQMLV	5962R9950401VZA,	WG14A	14LD CERAMIC SOIC
	100k rd(Si)		
LM124AWLQMLV	5962L9950401VDA,	W14B	14LD CERPACK
	50k rd(Si)		
LM124AWRQMLV	5962R9950401VDA,	W14B	14LD CERPACK
	100k rd(Si)		

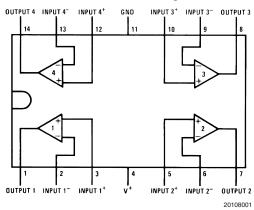
Connection Diagrams

Leadless Chip Carrier

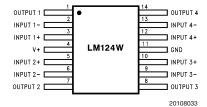


See NS Package Number E20A

Dual-In-Line Package

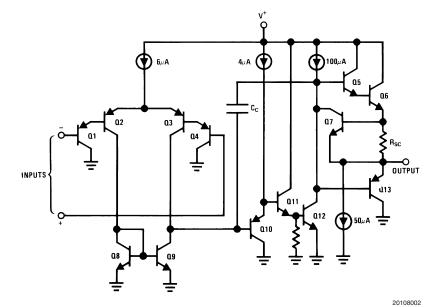


Top View See NS Package Number J14A



See NS Package Number W14B or WG14A

Schematic Diagram (Each Amplifier)



Absolute Maximum Ratings (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/ Distributors for availability and specifications.

Differential Input Voltage 32Vdc Input Voltage -0.3Vdc to $+32\text{Vdc}$ Input Current $(V_{IN} < -0.3\text{Vdc})$ (Note 4) 50 mA Power Dissipation (Note 2) $CERDIP$ 1260mW $CERPACK$ 700mW LCC 1350mW $CERAMIC SOIC$ 700mW $CERAMIC SOIC$ 700mW $COMETICAL COMETICAL COMETI$
Input Current $(V_{IN} < -0.3 \text{Vdc}) \text{ (Note 4)} \qquad \qquad 50 \text{ mA}$ Power Dissipation (Note 2) $CERDIP \qquad \qquad 1260 \text{mW}$ $CERPACK \qquad \qquad 700 \text{mW}$ $LCC \qquad \qquad 1350 \text{mW}$ $CERAMIC SOIC \qquad \qquad 700 \text{mW}$ $CERAMIC SOIC \qquad \qquad 700 \text{mW}$ $Output Short-Circuit to GND \qquad \qquad$
$(V_{IN} < -0.3Vdc) \text{ (Note 4)} \\ \text{Power Dissipation (Note 2)} \\ \text{CERDIP} & 1260mW \\ \text{CERPACK} & 700mW \\ \text{LCC} & 1350mW \\ \text{CERAMIC SOIC} & 700mW \\ \text{Output Short-Circuit to GND} \\ \text{(One Amplifier) (Note 3)} \\ V^+ \le 15Vdc \text{ and } T_A = 25^{\circ}C & \text{Continuous} \\ \text{Operating Temperature Range} & -55^{\circ}C \le T_A \le +125^{\circ}C \\ \text{Maximum Junction Temperature} & 150^{\circ}C \\ \text{Storage Temperature Range} & -65^{\circ}C \le T_A \le +150^{\circ}C \\ \text{Lead Temperature (Soldering, 10 seconds)} & 260^{\circ}C \\ \text{Thermal Resistance ThetaJA} \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\$
$\begin{tabular}{lllllllllllllllllllllllllllllllllll$
$\begin{array}{lll} \text{CERDIP} & 1260\text{mW} \\ \text{CERPACK} & 700\text{mW} \\ \text{LCC} & 1350\text{mW} \\ \text{CERAMIC SOIC} & 700\text{mW} \\ \text{Output Short-Circuit to GND} & & & \\ \text{(One Amplifier) (Note 3)} & & & \\ V^+ \leq 15\text{Vdc and T}_A = 25^{\circ}\text{C} & \text{Continuous} \\ \text{Operating Temperature Range} & -55^{\circ}\text{C} \leq T_A \leq +125^{\circ}\text{C} \\ \text{Maximum Junction Temperature} & 150^{\circ}\text{C} \\ \text{Storage Temperature Range} & -65^{\circ}\text{C} \leq T_A \leq +150^{\circ}\text{C} \\ \text{Lead Temperature (Soldering, 10 seconds)} & 260^{\circ}\text{C} \\ \end{array}$
$\begin{array}{lll} \text{CERPACK} & 700\text{mW} \\ \text{LCC} & 1350\text{mW} \\ \text{CERAMIC SOIC} & 700\text{mW} \\ \text{Output Short-Circuit to GND} & \\ & (\text{One Amplifier}) \text{ (Note 3)} \\ V^+ \leq 15\text{Vdc and T}_A = 25^{\circ}\text{C} & \text{Continuous} \\ \text{Operating Temperature Range} & -55^{\circ}\text{C} \leq T_A \leq +125^{\circ}\text{C} \\ \text{Maximum Junction Temperature} & 150^{\circ}\text{C} \\ \text{Storage Temperature Range} & -65^{\circ}\text{C} \leq T_A \leq +150^{\circ}\text{C} \\ \text{Lead Temperature (Soldering, 10 seconds)} & 260^{\circ}\text{C} \\ \end{array}$
LCC1350mWCERAMIC SOIC700mWOutput Short-Circuit to GND (One Amplifier) (Note 3) $V^+ \le 15Vdc$ and $T_A = 25^{\circ}C$ ContinuousOperating Temperature Range $-55^{\circ}C \le T_A \le +125^{\circ}C$ Maximum Junction Temperature $150^{\circ}C$ Storage Temperature Range $-65^{\circ}C \le T_A \le +150^{\circ}C$ Lead Temperature (Soldering, 10 seconds) $260^{\circ}C$ Thermal Resistance ThetaJA
CERAMIC SOIC 700mW Output Short-Circuit to GND (One Amplifier) (Note 3) $V^+ \leq 15 \text{Vdc and T}_A = 25^{\circ}\text{C} \qquad \qquad \text{Continuous} \\ \text{Operating Temperature Range} \qquad \qquad -55^{\circ}\text{C} \leq T_A \leq +125^{\circ}\text{C} \\ \text{Maximum Junction Temperature} \qquad \qquad \qquad 150^{\circ}\text{C} \\ \text{Storage Temperature Range} \qquad \qquad -65^{\circ}\text{C} \leq T_A \leq +150^{\circ}\text{C} \\ \text{Lead Temperature (Soldering, 10 seconds)} \qquad \qquad 260^{\circ}\text{C} \\ \text{Thermal Resistance ThetaJA}$
Output Short-Circuit to GND (One Amplifier) (Note 3) $V^{+} \leq 15 V dc \text{ and } T_A = 25 ^{\circ}C $ Continuous Operating Temperature Range $-55 ^{\circ}C \leq T_A \leq +125 ^{\circ}C$ Maximum Junction Temperature $150 ^{\circ}C$ Storage Temperature Range $-65 ^{\circ}C \leq T_A \leq +150 ^{\circ}C$ Lead Temperature (Soldering, 10 seconds) $260 ^{\circ}C$ Thermal Resistance ThetaJA
(One Amplifier) (Note 3) $V^{+} \le 15 \text{Vdc and T}_{A} = 25 ^{\circ}\text{C} \qquad \qquad \text{Continuous}$ Operating Temperature Range $-55 ^{\circ}\text{C} \le T_{A} \le +125 ^{\circ}\text{C}$ Maximum Junction Temperature $150 ^{\circ}\text{C}$ Storage Temperature Range $-65 ^{\circ}\text{C} \le T_{A} \le +150 ^{\circ}\text{C}$ Lead Temperature (Soldering, 10 seconds) $260 ^{\circ}\text{C}$ Thermal Resistance ThetaJA
$\begin{array}{lll} V^+ \le 15 V dc \ and \ T_A = 25 ^\circ C & Continuous \\ Operating \ Temperature \ Range & -55 ^\circ C \le T_A \le +125 ^\circ C \\ Maximum \ Junction \ Temperature & 150 ^\circ C \\ Storage \ Temperature \ Range & -65 ^\circ C \le T_A \le +150 ^\circ C \\ Lead \ Temperature \ (Soldering, \ 10 \ seconds) & 260 ^\circ C \\ Thermal \ Resistance \ ThetaJA & $
Operating Temperature Range $-55^{\circ}\text{C} \le T_{\text{A}} \le +125^{\circ}\text{C}$ Maximum Junction Temperature 150°C Storage Temperature Range $-65^{\circ}\text{C} \le T_{\text{A}} \le +150^{\circ}\text{C}$ Lead Temperature (Soldering, 10 seconds) 260°C Thermal Resistance ThetaJA
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Storage Temperature Range $-65^{\circ}\text{C} \le \text{T}_{\text{A}} \le +150^{\circ}\text{C}$ Lead Temperature (Soldering, 10 seconds) 260°C Thermal Resistance ThetaJA
Lead Temperature (Soldering, 10 seconds) 260°C Thermal Resistance ThetaJA
Thermal Resistance ThetaJA
APPRIN (OWN ALL)
CERDIP (Still Air) 103 C/W
(500LF/Min Air flow) 51 C/W
CERPACK (Still Air) 176 C/W
(500LF/Min Air flow) 116 C/W
LCC (Still Air) 91 C/W
(500LF/Min Air flow) 66 C/W
CERAMIC SOIC (Still Air) 176 C/W
(500LF/Min Air flow) 116 C/W
ThetaJC
CERDIP 19 C/W
CERPACK 18 C/W
LCC 24 C/W
CERAMIC SOIC 18 C/W
Package Weight (Typical)
CERDIP 2200mg
CERPACK 460mg
LCC 470mg
CERAMIC SOIC 410mg
ESD Tolerance (Note 5) 250V

Note 1: Absolute Maximum Ratings indicate limits beyond which damage to the device may occur. Operating Ratings indicate conditions for which the device is functional, but do not guarantee specific performance limits. For guaranteed specifications and test conditions, see the Electrical Characteristics. The guaranteed specifications apply only for the test conditions listed. Some performance characteristics may degrade when the device is not operated under the listed test conditions.

Note 2: The maximum power dissipation must be derated at elevated temperatures and is dictated by Tjmax (maximum junction temperature), ThetaJA (package junction to ambient thermal resistance), and TA (ambient temperature). The maximum allowable power dissipation at any temperature is Pdmax = (Tjmax - TA)/ThetaJA or the number given in the Absolute Maximum Ratings, whichever is lower.

Note 3: Short circuits from the output to V+ can cause excessive heating and eventual destruction. When considering short circuits to ground, the maximum output current is approximately 40mA independent of the magnitude of V+. At values of supply voltage in excess of +15Vdc, continuous short-circuits can exceed the power dissipation ratings and cause eventual destruction. Destructive dissipation can result from simultaneous shorts on all amplifiers.

Note 4: This input current will only exist when the voltage at any of the input leads is driven negative. It is due to the collector-base junction of the input PNP transistors becoming forward biased and thereby acting as input diode clamps. In addition to this diode action, there is also lateral NPN parasitic transistor action on the IC chip. This transistor action can cause the output voltages of the op amps to go to the V+ voltage level (or to ground for a large overdrive) for the time duration that an input is driven negative. This is not destructive and normal output states will re-establish when the input voltage, which was negative, again returns to a value greater than -0.3Vdc (at 25 C).

Note 5: Human body model, 1.5 k $\!\Omega$ in series with 100 pF.

Quality Conformance Inspection

MIL-STD-883, Method 5005 — Group A

Subgroup	Description	Temp (°C)
1	Static tests at	+25
2	Static tests at	+125
3	Static tests at	-55
4	Dynamic tests at	+25
5	Dynamic tests at	+125
6	Dynamic tests at	-55
7	Functional tests at	+25
8A	Functional tests at	+125
8B	Functional tests at	-55
9	Switching tests at	+25
10	Switching tests at	+125
11	Switching tests at	-55

LM124A 883 DC Electrical Characteristics

(The following conditions apply to all the following parameters, unless otherwise specified.) All voltages referenced to device ground.

SYMBOL	PARAMETER	CONDITIONS	NOTES	MIN	MAX	UNIT	SUB- GROUPS
Icc	Power Supply Current	V+ = 5V			1.2	mA	1, 2, 3
		V+ = 30V			3.0	mA	1
					4.0	mA	2, 3
Isink	Output Sink Current	V+ = 15V, Vout = 200mV, +Vin = 0mV, -Vin = +65mV		12		uA	1
		V+ = 15V, Vout = 2V,		10		mA	1
		+Vin = 0mV, -Vin = +65mV		5		mA	2, 3
Isource	Output Source	V+ = 15V, Vout = 2V,			-20	mA	1
	Current	+Vin = 0mV, -Vin = -65mV			-10	mA	2, 3
los	Short Circuit Current	V+ = 5V, Vout = 0V		-60		mA	1
Vio	Input Offset Voltage	V+ = 30V, Vcm = 0V		-2	2	mV	1
				-4	4	mV	2, 3
		V+ = 30V, Vcm = 28.5V		-2	2	mV	1
		V+ = 30V, Vcm = 28V		-4	4	mV	2, 3
		V+ = 5V, Vcm = 0V		-2	2	mV	1
				-4	4	mV	2, 3
CMRR	Common Mode Rejection Ratio	V+ = 30V, Vin = 0V to 28.5V		70		dB	1
±lib	Input Bias Current	V+ = 5V, Vcm = 0V		-50	10	nA	1
				-100	10	nA	2, 3
lio	Input Offset Current	V+ = 5V, Vcm = 0V		-10	10	nA	1
				-30	30	nA	2, 3
PSRR	Power Supply Rejection Ratio	V+ = 5V to 30V, Vcm = 0V		65		dB	1
Vcm	Common Mode	V+ = 30V	(Note 6)		28.5	V	1
	Voltage Range		(Note 6)		28	V	2, 3
Avs	Large Signal Gain	V+ = 15V, RI = 2K Ohms,	(Note 7)	50		V/mV	4
		Vo = 1V to 11V	(Note 7)	25		V/mV	5, 6
Voh	Output Voltage High	V+ = 30V, RI = 2K Ohms		26		V	4, 5, 6
		V+ = 30V, RI = 10K Ohms		27		V	4, 5, 6
Vol	Output Voltage Low	V+ = 30V, RI = 10K Ohms			40	mV	4, 5, 6
		V+ = 30V, Isink = 1uA			40	mV	4
					100	mV	5, 6
		V+ = 5V, RI = 10K Ohms			20	mV	4, 5, 6
	Channel Separation Amp to Amp Coupling	1KHz, 20KHz	(Note 8)	80		dB	4

LM124 883 DC Electrical Characteristics

(The following conditions apply to all the following parameters, unless otherwise specified.) All voltages referenced to device ground.

SYMBOL	PARAMETER	CONDITIONS	NOTES	MIN	MAX	UNIT	SUB- GROUPS
Icc	Power Supply Current	V+ = 5V			1.2	mA	1, 2, 3
		V+ = 30V			3.0	mA	1
					4.0	mA	2, 3
Isink	Output Sink Current	V+ = 15V, Vout = 200mV, +Vin = 0mV, -Vin = +65mV		12		uA	1
		V+ = 15V, Vout = 2V,		10		mA	1
		+Vin = 0mV, -Vin = +65mV		5		mA	2, 3
Isource	Output Source	V+ = 15V, Vout = 2V,			-20	mA	1
	Current	+Vin = 0mV, -Vin = -65mV			-10	mA	2, 3
los	Short Circuit Current	V+ = 5V, Vout = 0V		-60		mA	1
Vio	Input Offset Voltage	V+ = 30V, Vcm = 0V		-5	5	mV	1
				-7	7	mV	2, 3
		V+ = 30V, Vcm = 28V		-5	5	mV	1
				-7	7	mV	2, 3
		V+ = 5V, Vcm = 0V		-5	5	mV	1
				-7	7	mV	2, 3
		V+ = 30V, Vcm = 28.5V		-5	5	mV	1
CMRR	Common Mode Rejection Ratio	V+ = 30V, Vin = 0V to 28.5V		70		dB	1
+lib	Input Bias Current	V+ = 5V, Vcm = 0V		-150	10	nA	1
				-300	10	nA	2, 3
lio	Input Offset Current	V+ = 5V, Vcm = 0V		-30	30	nA	1
				-100	100	nA	2, 3
PSRR	Power Supply Rejection Ratio	V+ = 5V to 30V, Vcm = 0V		65		dB	1
Vcm	Common Mode	V+ = 30V	(Note 6)		28.5	V	1
	Voltage Range		(Note 6)		28	V	2, 3
Avs	Large Signal Gain	V+ = 15V, RI = 2K Ohms,		50		V/mV	4
		Vo = 1V to 11V		25		V/mV	5, 6
Voh	Output Voltage High	V+ = 30V, RI = 2K Ohms		26		V	4, 5, 6
		V+ = 30V, RI = 10K Ohms		27		V	4, 5, 6
Vol	Output Voltage Low	V+ = 30V, RI = 10K Ohms			40	mV	4, 5, 6
		V+ = 30V, Isink = 1uA			40	mV	4
					100	mV	5, 6
		V+ = 5V, RI = 10K Ohms			20	mV	4, 5, 6
	Channel Separation (Amp to Amp Coupling)	1KHz, 20KHz	(Note 8)	80		dB	4

LM124A RAD HARD DC Electrical Characteristics (Note 10)

(The following conditions apply to all the following parameters, unless otherwise specified.) All voltages referenced to device ground.

SYMBOL	PARAMETER	CONDITIONS	NOTES	MIN	MAX	UNIT	SUB- GROUPS
Vio	Input Offset Voltage	Vcc+ = 30V, Vcc- = Gnd,		-2	2	mV	1
		Vcm = -15V		-4	4	mV	2, 3
		Vcc+ = 2V, Vcc- = -28V,		-2	2	mV	1
		Vcm = 13V		-4	4	mV	2, 3
		Vcc+ = 5V, Vcc- = Gnd,		-2	2	mV	1
		Vcm = -1.4V		-4	4	mV	2, 3
		Vcc+ = 2.5V, Vcc- = -2.5,		-2	2	mV	1
		Vcm = 1.1V		-4	4	mV	2, 3
lio	Input Offset Current	Vcc+ = 30V, Vcc- = Gnd,		-10	10	nA	1, 2
		Vcm = -15V		-30	30	nA	3
		Vcc+ = 2V, Vcc- = -28V,		-10	10	nA	1, 2
		Vcm = 13V		-30	30	nA	3
		Vcc+ = 5V, Vcc- = Gnd,		-10	10	nA	1, 2
		Vcm = -1.4V		-30	30	nA	3
		Vcc+ = 2.5V, Vcc- = -2.5,		-10	10	nA	1, 2
		Vcm = 1.1V		-30	30	nA	3
±lib	Input Bias Current	Vcc+ = 30V, Vcc- = Gnd,		-50	+0.1	nA	1, 2
		Vcm = -15V		-100	+0.1	nA	3
		Vcc+ = 2V, Vcc- = -28V,		-50	+0.1	nA	1, 2
		Vcm = 13V		-100	+0.1	nA	3
		Vcc+ = 5V, Vcc- = Gnd,		-50	+0.1	nA	1, 2
		Vcm = -1.4V		-100	+0.1	nA	3
		Vcc+ = 2.5V, Vcc- = -2.5,		-50	+0.1	nA	1, 2
		Vcm = 1.1V		-100	+0.1	nA	3
+PSRR	Power Supply Rejection Ratio	Vcc- = Gnd, Vcm = -1.4V, 5V ≤ Vcc ≤ 30V		-100	100	uV/V	1, 2, 3
CMRR	Common Mode Rejection Ratio			76		dB	1, 2, 3
los+	Output Short Circiut Current	Vcc+ = 30V, Vcc- = Gnd, Vo = 25V		-70		mA	1, 2,3
Icc	Power Supply Current	Vcc+ = 30V, Vcc- = Gnd			3	mA	1, 2
					4	mA	3
Delta Vio/ Delta T	Input Offset Voltage Temperature Sensitivity	+25°C ≤ TA ≤ +125°C, +Vcc = 5V, -Vcc = 0V, Vcm = -1.4V	(Note 9)	-30	30	uV/ °C	2
		-55°C ≤ TA ≤ +25°C, +Vcc = 5V, -Vcc = 0V, Vcm = -1.4V	(Note 9)	-30	30	uV/ °C	3
Delta lio/ Delta T	Input Offset Current Temperature Sensitivity	+25°C ≤ TA ≤ +125°C, +Vcc = 5V, -Vcc = 0V, Vcm = -1.4V	(Note 9)	-400	400	pA/° C	2
		-55° C \leq TA \leq +25 $^{\circ}$ C, +Vcc = 5V, -Vcc = 0V, Vcm = -1.4V	(Note 9)	-700	700	pA/ °C	3

LM124A RAD HARD AC/DC Electrical Characteristics (Note 10)

(The following conditions apply to all the following parameters, unless otherwise specified.) All voltages referenced to device ground.

SYMBOL	PARAMETER	CONDITIONS	NOTES	MIN	MAX	UNIT	SUB- GROUPS
Vol	Logical "0" Output Voltage	Vcc+ = 30V, Vcc- = Gnd, RI = 10K Ohms			35	mV	4, 5, 6
		Vcc+ = 30V, Vcc- = Gnd, lol = 5mA			1.5	V	4, 5, 6
		Vcc+ = 4.5V, Vcc- = Gnd, lol = 2uA			0.4	V	4, 5, 6
Voh	Logical "1" Output Voltage	Vcc+ = 30V, Vcc- = Gnd, loh = -10mA		27		V	4, 5, 6
		Vcc+ = 4.5V, Vcc- = Gnd, loh = -10mA		2.4		V	4, 5, 6
		Vcc+ = 30V, Vcc- = Gnd,		50		V/mV	4
Avs+	Voltage Gain	1V ≤ Vo ≤ 26V, RI = 10K Ohms		25		V/mV	5, 6
		Vcc+ = 30V, Vcc- = Gnd,		50		V/mV	4
		5V ≤ Vo ≤ 20V, RI = 2K Ohms		25		V/mV	5, 6
Avs	Voltage Gain	Vcc+ = 5V, Vcc- = Gnd, 1V ≤ Vo ≤ 2.5V, RI = 10K Ohms		10		V/mV	4, 5, 6
		Vcc+ = 5V, Vcc- = Gnd, 1V ≤ Vo ≤ 2.5V, RI = 2K Ohms		10		V/mV	4, 5, 6
+Vop	Maximum Output Voltage Swing	Vcc+ = 30V, Vcc- = Gnd, Vo = +30V, RI = 10K Ohms		27		V	4, 5, 6
		Vcc+ = 30V, Vcc- = Gnd, Vo = +30V, RI = 2K Ohms		26		V	4, 5, 6
TR(tr)	Transient Response: Rise Time	Vcc+ = 30V, Vcc- = Gnd			1	uS	7, 8A, 8B
TR(os)	Transient Response: Overshoot	Vcc+ = 30V, Vcc- = Gnd			50	%	7, 8A, 8B
±Sr	Slew Rate: Rise	Vcc+ = 30V, Vcc- = Gnd		0.1		V/uS	7, 8A, 8B
	Slew Rate: Fall	Vcc+ = 30V, Vcc- = Gnd		0.1		V/uS	7, 8A, 8B

LM124A RAD HARD — AC Electrical Characteristics (Note 10)

(The following conditions apply to all the following parameters, unless otherwise specified.) AC: +Vcc = 30V, -Vcc = 0V

SYMBOL	PARAMETER	CONDITIONS	NOTES	MIN	MAX	UNIT	SUB- GROUPS
NI(BB)	Noise Broadband	+Vcc = 15V, -Vcc = -15V, BW = 10Hz to 5KHz			15	uVrm s	7
NI(PC)	Noise Popcorn	+Vcc = 15V, -Vcc = -15V, Rs = 20K Ohms, BW = 10Hz to 5KHz			50	uVpK	7
Cs	Channel Separation	+Vcc = 30V, -Vcc = Gnd, RI = 2K Ohms		80		dB	7
		RI = 2K Ohms, Vin = 1V and 16V, A to B		80		dB	7
		RI = 2K Ohms, Vin = 1V and 16V, A to C		80		dB	7
		RI = 2K Ohms, Vin = 1V and 16V, A to D		80		dB	7
		RI = 2K Ohms, Vin = 1V and 16V, B to A		80		dB	7
		RI = 2K Ohms, Vin = 1V and 16V, B to C		80		dB	7
		RI = 2K Ohms, Vin = 1V and 16V, B to D		80		dB	7
		RI = 2K Ohms, Vin = 1V and 16V, C to A		80		dB	7
		RI = 2K Ohms, Vin = 1V and 16V, C to B		80		dB	7
		RI = 2K Ohms, Vin = 1V and 16V, C to D		80		dB	7
		RI = 2K Ohms, Vin = 1V and 16V, D to A		80		dB	7
		RI = 2K Ohms, Vin = 1V and 16V, D to B		80		dB	7
		RI = 2K Ohms, Vin = 1V and 16V, D to C		80		dB	7

LM124A RAD HARD — DC Drift Values (Note 10)

(The following conditions apply to all the following parameters, unless otherwise specified.) **DC: "Delta calculationsperformed on QMLV devices at group B, subgroup 5 only"**

SYMBOL	PARAMETER	CONDITIONS	NOTES	MIN	MAX	UNIT	SUB-
							GROUPS
Vio	Input Offset Voltage	Vcc+ = 30V, Vcc- = Gnd,		-0.5	0.5	mV	1
		Vcm = -15V					
±lib	Input Bias Current	Vcc+ = 30V, Vcc- = Gnd,		-10	10	nA	1
		Vcm = -15V					

Electrical Characteristics — POST RADIATION LIMITS +25°C (Note 10)

(The following conditions apply to all the following parameters, unless otherwise specified.) All voltages referenced to device ground.

SYMBOL	PARAMETER	CONDITIONS	NOTES	MIN	MAX	UNIT	SUB- GROUPS
Vio	Input Offset Voltage	Vcc+ = 30V, Vcc- = Gnd, Vcm = -15V	(Note 10)	-2.5	2.5	mV	1
		Vcc+ = 2V, Vcc- = -28V, Vcm = 13V	(Note 10)	-2.5	2.5	mV	1
		Vcc+ = 5V, Vcc- = GND, Vcm = -1.4V	(Note 10)	-2.5	2.5	mV	1
		Vcc+ = 2.5V, Vcc- = -2.5, Vcm = 1.1V	(Note 10)	-2.5	2.5	mV	1
lio	Input Offset Current	Vcc+ = 30V, Vcc- = GND, Vcm = -15V	(Note 10)	-15	15	nA	1
		Vcc+ = 2V, Vcc- = -28V, Vcm = 13V	(Note 10)	-15	15	nA	1
		Vcc+ = 5V, Vcc- = GND, Vcm = -1.4V	(Note 10)	-15	15	nA	1
		Vcc+ = 2.5V, Vcc- = -2.5V, Vcm = 1.1V	(Note 10)	-15	15	nA	1
±lib	Input Bias Current	Vcc+ = 30V, Vcc- = GND, Vcm = -15V	(Note 10)	-75	+0.1	nA	1
		Vcc+ = 2V, Vcc- = -28V, Vcm = 13V	(Note 10)	-75	+0.1	nA	1
		Vcc+ = 5V, Vcc- = GND, Vcm = -1.4V	(Note 10)	-75	+0.1	nA	1
		Vcc+ = 2.5V, Vcc- = -2.5V, Vcm = 1.1V	(Note 10)	-75	+0.1	nA	1
Avs+	Voltage Gain	Vcc+ = 30V, Vcc- = GND, 1V ≤ Vo ≤ 26V, RI = 10K Ohms	(Note 10)	40		V/mV	4
		$Vcc+ = 30V$, $Vcc- = GND$, $5V \le Vo \le 20V$, $RI = 2K$ Ohms	(Note 10)	40		V/mV	4

Note 6: Guaranteed by Vio tests.

Note 7: Datalog reading in K=V/mV

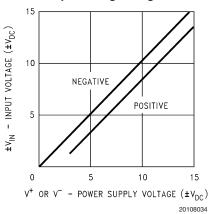
Note 8: Guaranteed, not tested

Note 9: Calculated parameters

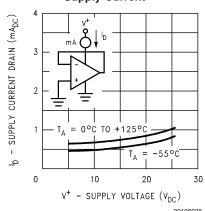
Note 10: Pre and post irradiation limits are identical to those listed under AC and DC electrical characteristics except as listed in the Post Radiation Limits Table. These parts may be dose rate sensitive in a space environment and demonstrate enhanced low dose rate effect. Radiation end point limits for the noted parameters are guaranteed only for the conditions as specified in MIL-STD-883, Method 1019

Typical Performance Characteristics

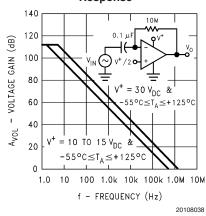




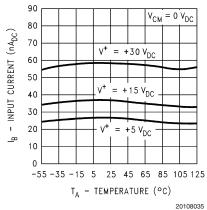
Supply Current



Open Loop Frequency Response

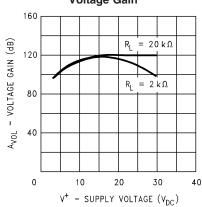


Input Current

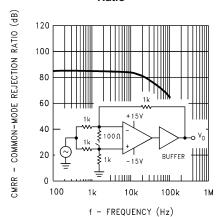


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Voltage Gain



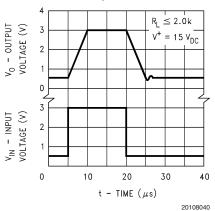
Common Mode Rejection Ratio



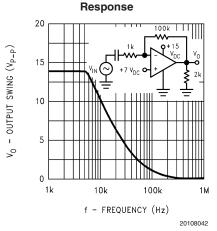
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Typical Performance Characteristics (Continued)

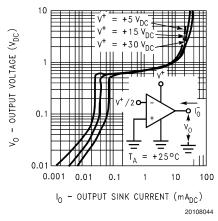
Voltage Follower Pulse Response



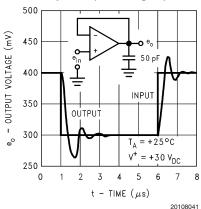
Large Signal Frequency



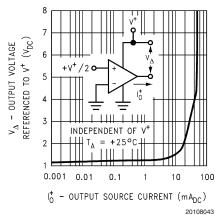
Output Characteristics Current Sinking



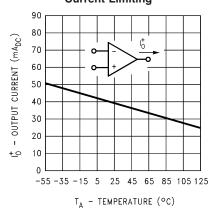
Voltage Follower Pulse Response (Small Signal)



Output Characteristics Current Sourcing



Current Limiting



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Application Hints

The LM124 series are op amps which operate with only a single power supply voltage, have true-differential inputs, and remain in the linear mode with an input common-mode voltage of 0 $V_{\rm DC}.$ These amplifiers operate over a wide range of power supply voltage with little change in performance characteristics. At $25\,^{\circ}\text{C}$ amplifier operation is possible down to a minimum supply voltage of $2.3~V_{\rm DC}.$

The pinouts of the package have been designed to simplify PC board layouts. Inverting inputs are adjacent to outputs for all of the amplifiers and the outputs have also been placed at the corners of the package (pins 1, 7, 8, and 14).

Precautions should be taken to insure that the power supply for the integrated circuit never becomes reversed in polarity or that the unit is not inadvertently installed backwards in a test socket as an unlimited current surge through the resulting forward diode within the IC could cause fusing of the internal conductors and result in a destroyed unit.

Large differential input voltages can be easily accommodated and, as input differential voltage protection diodes are not needed, no large input currents result from large differential input voltages. The differential input voltage may be larger than V $^{+}$ without damaging the device. Protection should be provided to prevent the input voltages from going negative more than $-0.3~V_{\rm DC}$ (at 25 $^{\circ}$ C). An input clamp diode with a resistor to the IC input terminal can be used.

To reduce the power supply drain, the amplifiers have a class A output stage for small signal levels which converts to class B in a large signal mode. This allows the amplifiers to both source and sink large output currents. Therefore both NPN and PNP external current boost transistors can be used to extend the power capability of the basic amplifiers. The output voltage needs to raise approximately 1 diode drop above ground to bias the on-chip vertical PNP transistor for output current sinking applications.

For ac applications, where the load is capacitively coupled to the output of the amplifier, a resistor should be used, from the output of the amplifier to ground to increase the class A bias current and prevent crossover distortion. Where the load is directly coupled, as in dc applications, there is no crossover distortion.

Capacitive loads which are applied directly to the output of the amplifier reduce the loop stability margin. Values of 50 pF can be accommodated using the worst-case noninverting unity gain connection. Large closed loop gains or resistive isolation should be used if larger load capacitance must be driven by the amplifier.

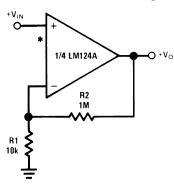
The bias network of the LM124 establishes a drain current which is independent of the magnitude of the power supply voltage over the range of from 3 $V_{\rm DC}$ to 30 $V_{\rm DC}$.

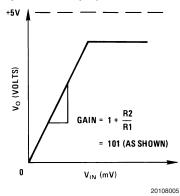
Output short circuits either to ground or to the positive power supply should be of short time duration. Units can be destroyed, not as a result of the short circuit current causing metal fusing, but rather due to the large increase in IC chip dissipation which will cause eventual failure due to excessive junction temperatures. Putting direct short-circuits on more than one amplifier at a time will increase the total IC power dissipation to destructive levels, if not properly protected with external dissipation limiting resistors in series with the output leads of the amplifiers. The larger value of output source current which is available at 25°C provides a larger output current capability at elevated temperatures (see typical performance characteristics) than a standard IC op amp.

The circuits presented in the section on typical applications emphasize operation on only a single power supply voltage. If complementary power supplies are available, all of the standard op amp circuits can be used. In general, introducing a pseudo-ground (a bias voltage reference of V+/2) will allow operation above and below this value in single power supply systems. Many application circuits are shown which take advantage of the wide input common-mode voltage range which includes ground. In most cases, input biasing is not required and input voltages which range to ground can easily be accommodated.

Typical Single-Supply Applications (V⁺ = 5.0 V_{DC})

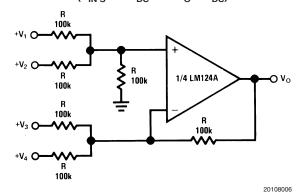
Non-Inverting DC Gain (0V Input = 0V Output)





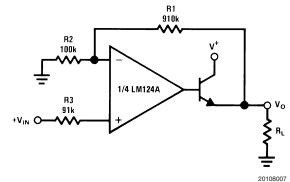
 ${}^{\star}\text{R}$ not needed due to temperature independent I_{IN}

DC Summing Amplifier (V_{IN'S} \geq 0 V_DC and V_O \geq V_DC)



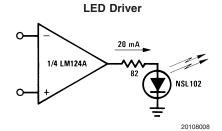
Where: $V_0 = V_1 + V_2 - V_3 - V_4$ $(V_1 + V_2) \ge (V_3 + V_4)$ to keep $V_0 > 0 V_{DC}$

Power Amplifier

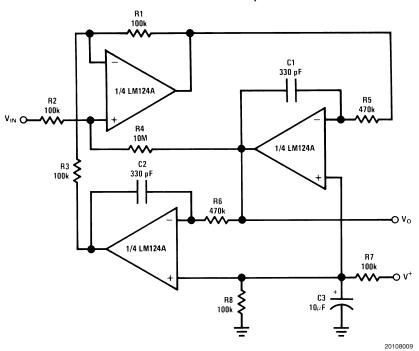


 $V_0 = 0 \ V_{DC} \text{ for } V_{IN} = 0 \ V_{DC}$ A_V = 10

Typical Single-Supply Applications (V⁺ = 5.0 V_{DC}) (Continued)



"BI-QUAD" RC Active Bandpass Filter



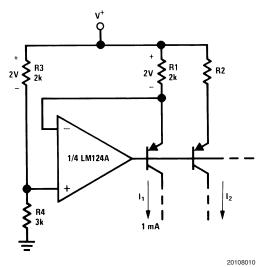
 $f_0 = 1 \text{ kHz}$

Q = 50

 $A_V = 100 (40 dB)$

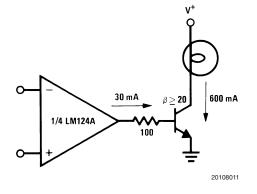
16

Fixed Current Sources

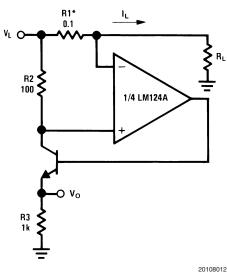


 $I_2 = \left(\frac{R1}{R2}\right)I_1$

Lamp Driver



Current Monitor

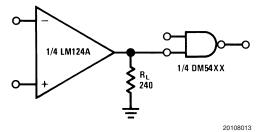


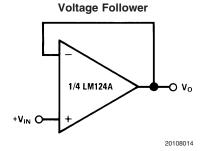
$$V_O = \frac{1V(I_L)}{1A}$$

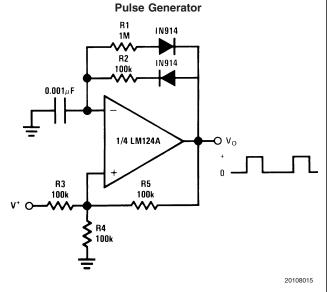
$$V_A \leq V_A^+ = 3V_A^+$$

*(Increase R1 for I_L small)

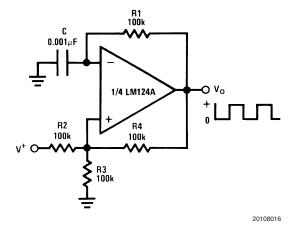
Driving TTL



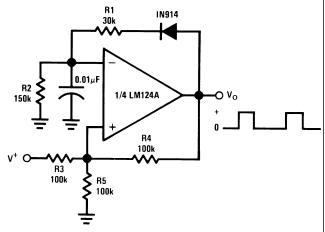




Squarewave Oscillator



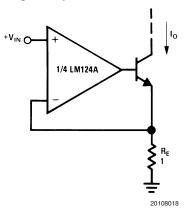
Pulse Generator



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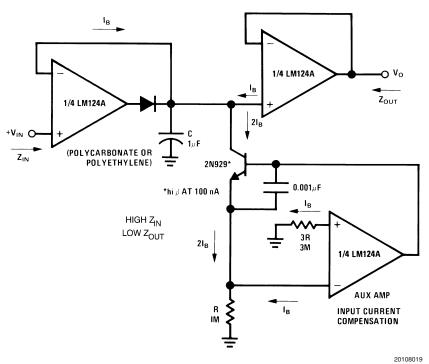
Typical Single-Supply Applications (V⁺ = 5.0 V_{DC}) (Continued)

High Compliance Current Sink



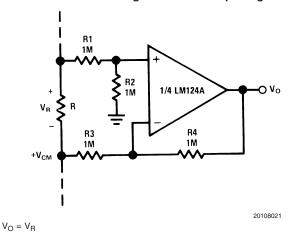
 $I_O = 1$ amp/volt V_{IN} (Increase R_E for I_o small)

Low Drift Peak Detector



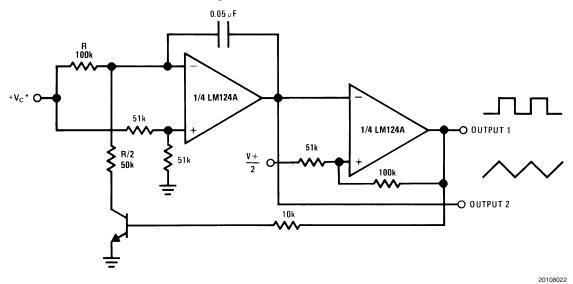
Comparator with Hysteresis

Ground Referencing a Differential Input Signal



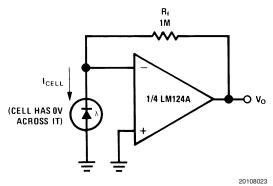
Voltage Controlled Oscillator Circuit

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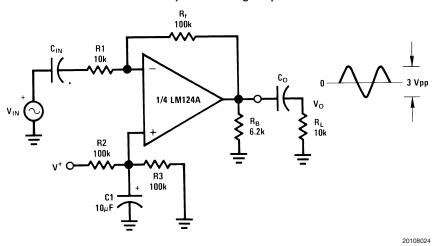
*Wide control voltage range: 0 $V_{DC} \le V_{C} \le 2$ (V⁺ -1.5 V_{DC})

Photo Voltaic-Cell Amplifier



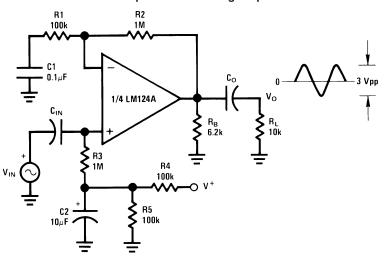
Typical Single-Supply Applications (V⁺ = 5.0 V_{DC}) (Continued)

AC Coupled Inverting Amplifier



 $A_V = \frac{R_f}{R1}$ (As shown, $A_V = 10$)

AC Coupled Non-Inverting Amplifier

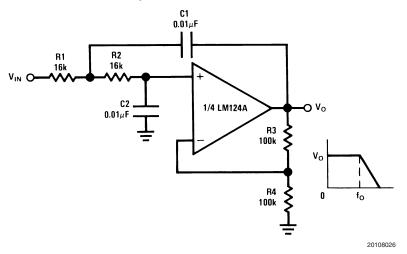


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$$A_V = 1 + \frac{R2}{R1}$$

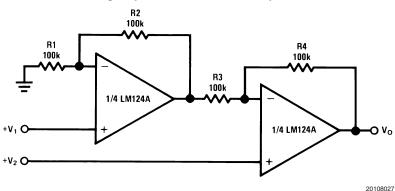
$$A_V = 11 \text{ (As shown)}$$

DC Coupled Low-Pass RC Active Filter



 $f_O = 1 \text{ kHz}$ Q = 1 $A_V = 2$

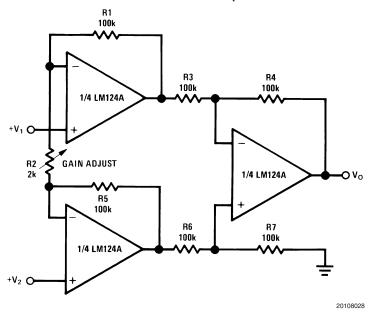
High Input Z, DC Differential Amplifier



For $\frac{R1}{R2} = \frac{R4}{R3}$ (CMRR depends on this resistor ratio match)

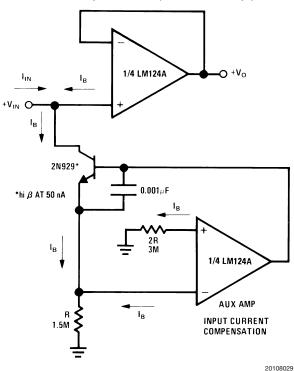
$$V_{O} = 1 + \frac{R4}{R3}(V_{2} - V_{1})$$
As shown: $V_{O} = 2(V_{2} - V_{1})$

High Input Z Adjustable-Gain DC Instrumentation Amplifier

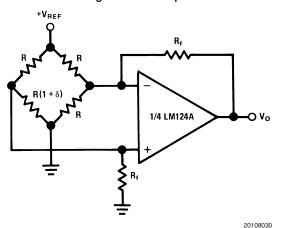


If R1 = R5 & R3 = R4 = R6 = R7 (CMRR depends on match)
$$V_O=1+\frac{2R1}{R2}(V_2-V_1)$$
 As shown $V_O=$ 101 (V_2-V_1)

Using Symmetrical Amplifiers to Reduce Input Current (General Concept)



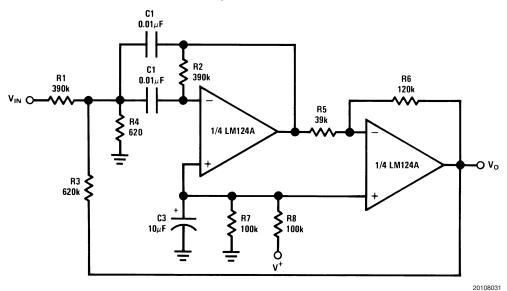
Bridge Current Amplifier



For $\delta <<$ 1 and $R_f >> R$ $V_O \cong V_{REF} \left(\frac{\delta}{2}\right) \frac{R_f}{R}$

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Bandpass Active Filter

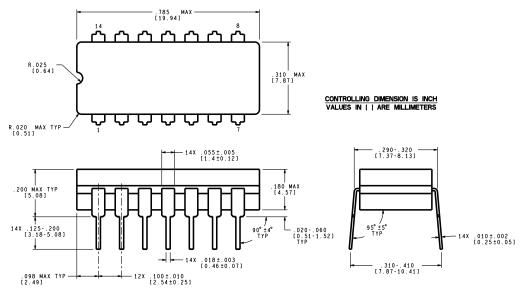


 $f_O = 1 \text{ kHz}$ Q = 25

Revision History Section

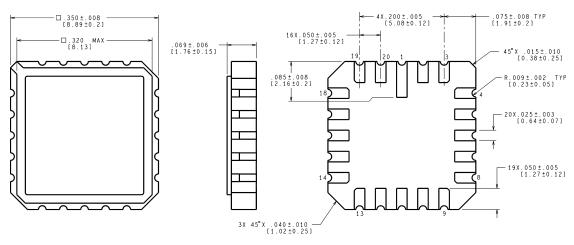
Date				
Released	Revision	Section	Originator	Changes
9/2/04	А	New Release, Corporate format	R. Malone	3 MDS data sheets converted into one
				Corp. data sheet format. MNLM124-X,
				Rev. 1A2, MNLM124A-X, Rev. 1A3 and
				MRLM124A-X-RH, Rev. 5A0. MDS data
				sheets will be archived.
01/27/05	В	Connection Diagrams, Quality	R. Malone	Added E package Connection Diagram.
		Conformance Inspection Section,		Changed verbiage under Quality
		and Physical Dimensions drawings		Conformance Title, and Updated
				Revisions for the Marketing Drawings.
04/18/05	С	Update Absolute Maximum Ratings	R. Malone	Corrected typo for Supply Voltage limit
		Section		From: 32Vdc or +16Vdc TO: 32Vdc or
				±16Vdc. Added cerpack, cerdip, LCC
				package weight.

Physical Dimensions inches (millimeters) unless otherwise noted



J14A (Rev J)

SAMPLE TEXT Ceramic Dual-In-Line Package (J) NS Package Number J14A

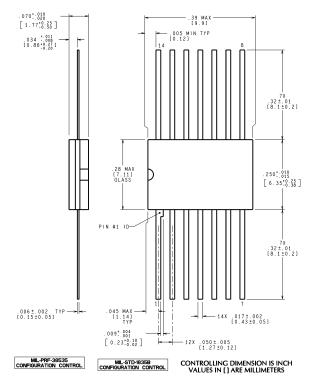


CONTROLLING DIMENSION IS INCH VALUES IN [] ARE MILLIMETERS

E20A (Rev F)

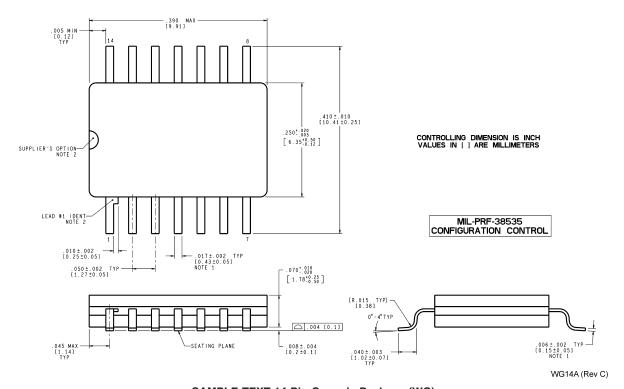
SAMPLE TEXT 20 Pin Leadless Chip Carrier, Type C (E) NS Package Number E20A

Physical Dimensions inches (millimeters) unless otherwise noted (Continued)



SAMPLE TEXT Ceramic Flatpak Package NS Package Number W14B

W14B (Rev P)



SAMPLE TEXT 14-Pin Ceramic Package (WG)
NS Package Number WG14A

LM124A/LM124QML Low Power Quad Operational Amplifiers

Notes

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